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UTILITY PATENT APPLICATION TRANSMITTAL

(Only for new nonprovisional applications under 37 CFR 1.53(b))

Attorney Docket No.

684.2728

First Named Inventor or Application Identifier

TOMOHARU HASE

Express Mail Label No.

APPLICATION ELEMENTS

See MPEP chapter 600 concerning utility patent application contents.

ADDRESS TO:

Assistant Commissioner for Patents
Box Patent Application
Washington, DC 20231

1. ☒ Fee Transmittal Form
(Submit an original, and a duplicate for fee processing)

2. ☒ Specification Total Pages 28

3. ☒ Drawing(s) (35 USC 113) Total Sheets 8

4. ☒ Oath or Declaration Total Pages 1

a. ☐ Newly executed (original or copy)

b. ☒ Unexecuted for information purposes

c. ☐ Copy from a prior application (37 CFR 1.63(d))
(for continuation/divisional with Box 17 completed)
(Note Box 5 below)

i. ☐ **DELETION OF INVENTOR(S)**
Signed Statement attached deleting inventor(s) named in
the prior application, see 37 CFR 1.63(d)(2) and 1.33(b).

6. ☐ Incorporation By Reference (useable if Box 4c is checked)
The entire disclosure of the prior application, from which a copy of the oath or
declaration is supplied under Box 4c, is considered as being part of the disclosure of
the accompanying application and is hereby incorporated by reference therein.

6. ☐ Microfiche Computer Program (Appendix)

7. Nucleotide and/or Amino Acid Sequence Submission
(if applicable, all necessary)

a. ☐ Computer Readable Copy

b. ☐ Paper Copy (identical to computer copy)

c. ☐ Statement verifying identity of above copies

ACCOMPANYING APPLICATION PARTS

8. ☐ Assignment Papers (cover sheet & documents)

9. ☐ 37 CFR 3.73(b) Statement ☐ Power of Attorney
(when there is an assignee)

10. ☐ English Translation Document (if applicable)

11. ☐ Information Disclosure Statement (IDS)/PTO-1449 ☐ Copies of IDS
Citations

12. ☐ Preliminary Amendment

13. ☒ Return Receipt Postcard (MPEP 503)
(Should be specifically itemized)

14. ☐ Small Entity Statement(s) ☐ Statement filed in prior application
Status still proper and desired

15. ☐ Certified Copy of Priority Document(s)
(if foreign priority is claimed)

16. ☐ Other: _____

17. If a CONTINUING APPLICATION, check appropriate box and supply the requisite information:

☐ Continuation

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18. CORRESPONDENCE ADDRESS

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CLAIMS	(1) FOR	(2) NUMBER FILED	(3) NUMBER EXTRA	(4) RATE	(5) CALCULATIONS
	TOTAL CLAIMS (37 CFR 1.16(c))	15-20 -	0	X \$ 22.00 -	\$ 0.00
	INDEPENDENT CLAIMS (37 cfr 1.16(b))	2-3 -	0	X \$ 82.00 -	\$ 0.00
	MULTIPLE DEPENDENT CLAIMS (if applicable) (37 CFR 1.16(d))			\$270.00 -	\$ 270.00
				BASIC FEE (37 CFR 1.16(a))	\$ 790.00
			Total of above Calculations -		\$1060.00
	Reduction by 50% for filing by small entity (Note 37 CFR 1.9, 1.27, 1.28).				
	TOTAL -				\$1060.00

19. Small entity status

- a. ☐ A Small entity statement is enclosed
- b. ☐ A small entity statement was filed in the prior nonprovisional application and such status is still proper and desired.
- c. ☐ Is no longer claimed.

20. ☒ A check in the amount of \$ 1060.00 to cover the filing fee is enclosed.

21. ☐ A check in the amount of \$ _____ to cover the recordal fee is enclosed.

22. The Commissioner is hereby authorized to credit overpayments or charge the following fees to Deposit Account No. 06-1205:

- a. ☒ Fees required under 37 CFR 1.16.
- b. ☐ Fees required under 37 CFR 1.17.
- c. ☐ Fees required under 37 CFR 1.18.

SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT REQUIRED	
NAME	Steven E. Warner, Reg. No. 33,326
SIGNATURE	
DATE	September 3, 1998

EXPOSURE APPARATUS AND
DEVICE MANUFACTURING METHOD

FIELD OF THE INVENTION AND RELATED ART

5 This invention relates to an exposure
apparatus and a device manufacturing method. More
particularly, the invention is concerned with an
exposure apparatus for use in an exposure process for
manufacture of various devices such as semiconductor
10 devices (e.g., ICs or LSIs), image pickup devices
(e.g., CCDs), display devices (e.g., liquid crystal
panels), or sensors (e.g., magnetic heads), for
example, and it is concerned with a device
manufacturing method for manufacturing devices such as
15 described above.

For further increases of integration and
operation speed of a solid device such as LSI, for
example, miniaturization of a circuit pattern is being
advanced. Currently, pattern formation uses a
20 lithographic process which is based on a reduction
projection exposure method having superiority in
productivity and resolution performance. In this
method, a circuit pattern of a mask is simultaneously
transferred to a workpiece such as a semiconductor
25 wafer by use of a projection lens. The limit
resolution performance is proportional to the
wavelength of exposure light and is in inverse

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proportion to the numerical aperture (NA) of the projection lens. In consideration of this, improvement of resolution has been attempted by enlargement of numerical aperture of the projection lens. However, further miniaturization of semiconductor device needs shortening of wavelength of exposure light.

Recently, in addition to illumination light of Hg lamp of e-line (wavelength $\lambda = 546$ nm), g-line ($\lambda = 435$ nm), h-line ($\lambda = 405$ nm) or i-line ($\lambda = 365$ nm), short wavelength excimer lasers (e.g., KrF excimer laser with $\lambda = 248$ nm) are used practically in exposure apparatus.

Even if a high resolution projection lens and a short wavelength and high luminance light source are used, uniform resolution is not attainable over the whole circuit pattern image as printed on a wafer unless the illuminance distribution (light intensity distribution) of light illuminating the photomask is not uniform. Thus, good pattern printing is not accomplished. For this reason, an illumination optical system of a projection exposure apparatus must provide illuminance uniformness of illumination light to be projected to a mask surface, to assure uniform exposure over the whole printing surface. To this end, conventionally an illumination optical system is disposed between a light source and a mask surface

which optical system comprises a condenser lens and an optical integrator including an optical fiber bundle or a lens array called a fly's eye lens. In excimer laser exposure apparatuses, as a result of use of larger numerical aperture of projection lens and a shorter wavelength of light source for higher resolution precision and productivity, it is much more important to maintain illuminance uniformness (not greater than $\pm 1\%$) than in other exposure apparatuses.

However, practically it is very difficult to maintain illuminance uniformness of not greater than $\pm 1\%$ for a long time period.

Short wavelength exposure light such as described above may be extracted out of a wide bandwidth range of a light source, comprising a Hg lamp, for example, by use of a filter for transmitting only a desired wavelength or a wavelength selective thin film (optical thin film deposited on a lens surface or a mirror surface for transmitting or reflecting a desired wavelength only). Exposure light emitted from a light source goes through an illumination optical system for illuminating a reticle and a projection optical system (projection lens) for imaging a fine pattern, as formed on the reticle, upon a photosensitive substrate, by which transfer and printing of the fine pattern onto the photosensitive substrate is performed. In exposure apparatuses,

because of miniaturization of pattern line width,
improvements of throughput and resolution are
required, and this necessitates use of higher power
exposure light and, additionally, narrowed bandwidth
5 of exposure light.

It is known that, in an exposure apparatus
using exposure light of i-line (wavelength $\lambda = 365$ nm)
and an exposure apparatus using exposure light of a
wavelength shorter than the i-line, as a result of the
10 shortening of wavelength, the exposure light causes
opto-chemical reaction between oxygen and impurities
in the air. There is an inconvenience that the
product (blurring materials) created by this reaction
adheres to a glass material to cause an opaque "blur"
15 on the glass material. As for such blurring material,
there may be ammonium sulfate $(\text{NH}_4)_2\text{SO}_4$, as a
representative, which can be produced when, for
example, sulfurous acid SO_2 absorbs energy of light
and turns into an excited state such that it reacts
20 with oxygen in the air (i.e., oxidized). Such
ammonium sulfate bears a white color, and it produces
a "blur" when deposited on the surface of an optical
component such as a lens or a mirror. In that case,
the exposure light is scattered or absorbed by
25 ammonium sulfate and, as a result, the transmission
factor of the optical system decreases.

Particularly, in short wavelength region as

of KrF excimer laser, for example, wherein the exposure light has a wavelength of about 248 nm which is shorter than the i-line, the exposure light may cause strong opto-chemical reaction. In addition to production of "blur" as described above, there may be a phenomenon that the exposure light causes further reaction of oxygen in the air to produce ozone such that both residual oxygen and produced ozone absorb the exposure light. This results in further decrease of light quantity (transmission factor) of exposure light which can reach the photosensitive substrate, and it causes reduction of throughput. Japanese Laid-Open Patent Application, Laid-Open No. 216000/1994 proposes use of a casing of sealingly closed structure which accommodates therein a barrel containing a glass member such as a lens, for example, the inside of the casing being filled with an inert gas to keep low oxygen density to thereby prevent ozone generation.

With this method, however, attenuation or variation of exposure light resulting from absorption of exposure light by "blur" or ozone can not be prevented sufficiently.

SUMMARY OF THE INVENTION

It is accordingly an object of the present invention to provide an exposure apparatus and/or a device manufacturing method by which any change in

illuminance or illuminance non-uniformness can be suppressed such that a substrate can be exposed constantly with correct exposure amount.

In accordance with an aspect of the present invention, there is provided an exposure apparatus, comprising: an illumination optical system for illuminating an original with ultraviolet light; a projection optical system for projecting a pattern of the original onto a substrate to be exposed; and gas purging means for replacing an inside space, where optical components of at least one of said illumination optical system and said projection optical system are placed, with a gas containing substantially no moisture or water content.

In accordance with another aspect of the present invention, there is provided an exposure apparatus, comprising: an illumination optical system for illuminating an original with ultraviolet light; a projection optical system for projecting a pattern of the original onto a substrate to be exposed; gas purging means for replacing an inside space, where optical components of at least one of said illumination optical system and said projection optical system are placed, with a particular gas; and passage means for mutually communicating spaces separated by said optical components, for gas purging.

In an illumination optical system or a

projection optical system of a reduction projection exposure apparatus, an anti-reflection film (optical thin film) is formed on the surface of an optical element such as a transparent plate, a lens or a prism, for example. The provision of such anti-reflection film is to efficiently direct light from a light source to a photosensitive substrate and also to prevent impingement of flare or ghost on the photosensitive substrate. However, due to the property, such anti-reflection film may easily absorb water content of gas. With an anti-reflection film having water content adhered thereto, the spectral reflection characteristic on the surface thereof or the absorption coefficient on the surface may change by a small amount, causing a change in spectral transmission factor. Usually, an illumination optical system and a projection optical system have optical elements with surfaces of a number of several tens in total. Thus, even if the change in spectral transmission factor per one surface is small, there may be a large change of spectral transmission factor in the whole optical system.

In accordance with the first aspect of the present invention, the ambience of optical components of the illumination optical system or the projection optical system may be replaced by a gas having substantially no water content, by gas purging. This

is effective to prevent a change in transmission factor of the whole optical system (i.e., a change in illuminance or illuminance non-uniformness) resulting from a change in spectral transmission factor due to
5 adhesion of water content to optical elements such as described above. Thus, a substrate can be exposed constantly with correct exposure amount.

Absorption of exposure light or generation of "blur" material in a case where oxygen or ozone is
10 present along the light path may be solved by accommodating optical components such as lenses in a casing of sealingly closed structure and by filling the casing inside with an inert gas to thereby keep a low oxygen density. However, in a barrel where lenses
15 are placed, there are spaces which are separated by lenses and the barrel structure. Proper gas replacement can not always be done within these spaces. Namely, it is not easy to effectively prevent absorption of exposure light or generation of "blur"
20 material.

In accordance with the second aspect of the present invention, the ambience of optical components of the illumination optical system or the projection optical system may be replaced by an inert gas, by gas
25 purging. Additionally, there may be passage means communicated with the casing inside or the barrel inside, by which a low oxygen density can be kept

within the spaces where glass materials are placed.
This effectively prevents oxidization reaction during
an opto-chemical reaction process, and avoids
generation of resultant product (blurring material).

5 Additionally, it effectively prevents or reduces ozone
generation due to reaction of oxygen by exposure
light.

These and other objects, features and
advantages of the present invention will become more
10 apparent upon a consideration of the following
description of the preferred embodiments of the
present invention taken in conjunction with the
accompanying drawings.

15 BRIEF DESCRIPTION OF THE DRAWINGS

Figure 1 is a schematic view of a general
structure of a projection exposure apparatus according
to an embodiment of the present invention.

20 Figure 2 is a schematic view of an inside
structure of an illumination optical system or a
projection optical system.

Figure 3 is a schematic view for explaining
passage of a purging air inside an illumination
optical system or a projection optical system.

25 Figure 4 is a graph for explaining changes in
transmission factor with respect to time, in a case
where laser irradiation and gas purging are not

performed and the apparatus is left for a while.

Figure 5 is a schematic view of a general structure of a projection exposure apparatus according to a second embodiment of the present invention.

5 Figure 6 is a schematic view of a general structure of an exposure apparatus according to a third embodiment of the present invention.

10 Figure 7 is a schematic view for explaining an example of inside structure of a casing and barrel of the Figure 6 embodiment.

Figure 8 is a schematic view of lenses to be used in the Figure 6 embodiment, with notches outside the effective light flux.

15 Figure 9 is a flow chart of microdevice manufacturing processes.

Figure 10 is a flow chart for explaining details of a wafer process included in the procedure of Figure 9.

20 DESCRIPTION OF THE PREFERRED EMBODIMENTS

25 A reduction projection exposure apparatus according to an embodiment of the present invention may comprise means for replacing an ambient air of optical components of an illumination optical system and/or a projection optical system with a gas such as N₂ gas, He gas or dry air, for example. This is effective to decrease the humidity inside the optical

system, to reduce adhesion of moisture (water content). Thus, a change in spectral reflection factor of anti-reflection films can be prevented, and the transmission factor of the optical system can be maintained substantially constant.

A sensor such as a humidity sensor, for example, for detecting the level of replacement by the gas purging may be provided inside the optical system, and the gas purging may be controlled on the basis of a signal from the sensor.

For efficient gas purging, an inlet port and an outlet port for the purging gas inside the optical system may be disposed along a non-straight line.

In each optical system, support members for supporting lenses are provided with passages for gas purging which passages are so formed that in adjacent support members the passages are not aligned along a straight line. This assures higher replacement efficiency inside the barrel.

A reduction projection exposure apparatus according to another embodiment of the present invention may provide an exposure apparatus wherein a mask is illuminated with exposure light from a light source through an illumination optical system and wherein a pattern formed on the mask is projected onto a photosensitive substrate through a projection optical system. The exposure apparatus may include an

optical element or elements disposed on a light path of exposure light from the exposure light source to the photosensitive substrate, and a casing for accommodating the optical element or elements therein.

5 The or each optical element is formed with a notch for positively defining a flow passage of gas between spaces inside the casing, being separated by the optical element.

10 In order to accomplish the second aspect of the invention, as an example, within the barrel where a number of lenses may be placed, the lens supports may be provided with flow passages for flowing inert gas into every space as separated by the lenses. Alternatively, pipe means may be used to define a flow
15 passage outside the barrel.

On the other hand, as a result of further miniaturization and further enlargement of throughput, projection exposure apparatuses have become bulky and complicated. Thus, for every unit, saving space as
20 much as possible is desired. In this respect, if a flow passage is formed in the lens support, the diameter of the barrel with respect to the effective light flux becomes larger. Further, using pipe means to provide a flow passage outside the barrel leads to
25 undesirable complexity and increase of cost.

In the above embodiment, in consideration of this, an end portion of a lens is cut to save the

space. More specifically, a notch may be defined outside the effective range of a lens or optical component which is used when in a projection exposure apparatus a reticle is illuminated with exposure light from a light source so that a pattern of the reticle is transferred to a wafer through a projection lens. This may be done to assure a flow passage for inert gas. This enables provision of a flow passage without use of specific components of pipe means and without enlargement of the barrel diameter. In recent years, scan type projection exposure apparatuses are practically developed. For these exposure apparatuses, since the effective light flux is small as compared with the projection exposure apparatus, the design may be easier.

Preferred embodiments of the present invention will now be described in conjunction with the drawings.

Figure 1 is a schematic view of a general structure of a projection exposure apparatus according to a first embodiment of the present invention. Denoted in the drawing at 1 is a light source which may comprise an excimer laser of KrF (248 nm), ArF (193 nm) or F₂ (157 nm), for example. Denoted at 2 and 3 are illumination optical systems. Denoted at M1, M2 and M3 are deflecting mirrors. The illumination optical system 2 or 3 may include a beam

shaping optical system for shaping and incoherency transforming the laser light from the light source 1, as well as a fly's eye lens for defining secondary light sources and a condenser lens, for example. The light from the illumination optical system 3 is projected to a reticle R, such that the reticle is projected onto a photosensitive substrate (wafer) W by means of a projection optical system 4. Denoted at 5 is an X-Y stage for holding the photosensitive substrate W, and it performs two-dimensional stepwise motion in X and Y directions. Each of the illumination optical systems 2 and 3 and the projection optical system 4 is provided with a gas supply tube and a gas discharging tube for replacing and purging the gas within the inside space thereof.

Figures 2 and 2 show the structure in the inside space of the illumination optical system 2 or 3 or of the projection optical system 4. A casing 20 for the optical system is provided with an inlet port 6 and an outlet port 7 which are formed in a side wall of the casing and to which tubes for gas purging are connected. Inside the casing 20, lenses 30 are supported by lens support members 31, respectively. For efficient and uniform replacement of the whole inside space with purging airs, each lens support 31 is formed with bores to provide purging air passages 32 which are so disposed that at adjacent lenses the

passages 32 are not aligned along a straight line. Namely, a straight line connecting the passages 32 of adjacent lens supports 31 is out of parallel to an optical axis of the lens 30. With this arrangement, the path of air flow defined from the inlet port 6 to the outlet port 7 is not straight.

Figure 4 illustrates changes in transmission factor with respect to time, in a case where the apparatus is left without laser projection and gas purging. With the elapse of time when the apparatus is left out of operation, the transmission factor of the optical system as a whole gradually decreases (curve A) or increases (curve B) and, at a certain level, it becomes substantially constant. Whether the transmission factor decreases or increases is determined, depending on the characteristic of the optical system.

The results shown in Figure 4 may be attributable to the phenomenon that the moisture contained in the ambient gas within the optical system is gradually deposited on lens surfaces by which the transmission factor is changed.

In this embodiment, dry N_2 or He gas or dry air, for example, is supplied from the purging inlet port, and the gas is then collected from the gas outlet port. Thus, the ambient gases inside the optical systems can be continuously purged, by which

the humidity inside the optical system can be lowered and variation of transmission factor can be prevented. As a result of this, the transmission factor of the optical system is substantially unchanged with the lapse of time.

Figure 5 is a schematic view of a general structure of a projection exposure apparatus according to another embodiment of the present invention. In Figure 5, the elements corresponding to those of Figure 1 are denoted by like numerals. Thus, description therefor will be omitted.

In Figure 5, denoted by 8, 9 and 10 are hygrometers disposed inside the optical systems, respectively, by which the level of replacement inside the optical systems can be monitored continuously. Purging tubes are provided with servo valves 12 - 17 as illustrated which can be opened and closed as controlled by a main controller 11. These valves are normally closed.

If any of the monitored replacement levels (levels of hygrometers 8, 9 and 10) is above a specified level as inputted into the main controller 11 beforehand, the main controller 11 supplies a gas purging start signal to corresponding one or ones of the servo valves 12 and 13, 14 and 15 or 16 and 17 to open it, whereby gas purging is initiated. If the replacement level becomes smaller than a particular

level for completion detection as inputted into the main controller 11 beforehand, the main controller 11 applies a gas purging completion signal to the corresponding servo valve to close the same. By this, gas purging is stopped. The gas purging may be completed in response to the elapse of a predetermined time from the gas purging start. Alternatively, completion detection based on replacement level and completion detection responsive to elapse of a predetermined time may be used in combination.

Figure 6 is a schematic view of the structure of an exposure apparatus according to a third embodiment of the present invention. This exposure apparatus includes an exposure light source 101, an illumination optical system 102, a projection optical system 104, a reticle (mask) R, a photosensitive substrate (wafer) W, and a substrate stage 105 on which the wafer W is placed. Among these components, the exposure apparatus major assembly excluding the exposure light source 101 is accommodated in a chamber 120 which is controlled at a constant temperature.

The exposure light source 101 may comprise an excimer laser of KrF (wavelength 248 nm), ArF (wavelength 193 nm) or F₂ (wavelength 157 nm), for example, for producing pulse light in ultraviolet region. In place of such excimer laser, an Hg lamp may be used as an exposure light source, and i-line

(wavelength 365 nm) may be used as exposure light.

The illumination optical system 102 comprises a number of optical elements such as lenses or mirrors, and it serves to illuminate an illumination region on the reticle R with uniform illuminance, with the exposure light from the exposure light source 101. This illumination optical system 102 is accommodated in two casings 110 and 111 which are sealingly closed. The illumination optical system 102 includes a beam shaping optical system 106, a zooming optical system (enlarging system) 107, a fly's eye lens 108 as an optical integrator, and an illumination system aperture stop 109 disposed at the exit of the fly's eye lens 108. The second casing 111 contains a condenser lens 112. Between the first casing 110 and the second casing 111, there is a blind 113 for determining the shape of the illumination region on the reticle R. At the portions of the first and second casings 110 and 111 which are on the path of exposure light (illumination light), there are transparent glass windows.

Details of the structural portions of the illumination optical system as well as the functions of them will be described. The exposure light emitted from the exposure light source 101 passes through the beam shaping optical system 106 by which the beam shape is changed from an oblong shape to a square

shape. Then, the light enters the zooming optical system (enlarging system) 107, whereby the exposure light is enlarged to a required size. The light then enters the fly's eye lens 108. The exit side end face of the fly's eye lens 108 is in an optically conjugate relation with the light source 2, and a secondary light source plane is defined there. Light rays emitted from the secondary light sources (elements) go through the aperture of the aperture stop 109 and the blind 113, by which the illumination region on the reticle R is restricted. The exposure light impinging on the condenser lens 112 is collected, and then it illuminates the reticle R which is placed in a positional relation of Fourier transformation with respect to the secondary light source plane. Thus, the individual elements of the fly's eye lens 108 illuminate the reticle R through the condenser lens 112, such that they serve as an optical integrator. As a result, the pattern region of the reticle R is illuminated uniformly.

The projection optical system 104 comprises a lens barrel and plural lens elements supported by the barrel. The projection optical system 104 has a pupil plane which is in an optically conjugate positional relation with the secondary light source plane and also in a positional relation of Fourier transformation with respect to the reticle surface.

Illumination light diffracted by the pattern on the reticle R enters the projection optical system 104, and diffraction light passing through an aperture stop (not shown), defined at the pupil plane of the projection optical system 104, serves to project the pattern of the reticle R onto the wafer W which is disposed at a position optically conjugate with the reticle R.

The substrate stage 105 for holding the wafer W can be moved two-dimensionally by means of a driving system, not shown. Thus, by performing exposures while stepping the substrate stage 105, the pattern of the reticle R can be transferred to different shot areas on the wafer W sequentially.

In the projection exposure apparatus of this embodiment as described above, a nitrogen supplying device 114 is connected to the casings 110 and 111 of the illumination optical system and to the projection optical system 104 through tubes, for supplying a dry inert gas (nitrogen N_2 gas) so as to keep a low "oxygen" density inside the casings 110 and 111 and the projection optical system 104. Also, a gas evacuating device 115 is connected to them through tubes, for discharging the inside airs or gases in them. Additionally, the nitrogen supplying device 114 and the gas discharging device 115 are connected to the inside of each barrel, constituting an optical

system accommodated in the casing and having a number of lenses therein, so that a low oxygen density is kept constantly also inside the barrel.

Figure 7 is an enlarged view showing an example of a casing 121 and a barrel 122 accommodated in the casing 121. As shown in Figure 7, the barrel has lenses 123a - 123d disposed therewithin. There are spaces 124a - 124e as separated by these lenses 123a - 123d. Mounted at the opposite ends of the barrel 122 are sheet glass members 125a and 125b as windows, and they are demountably mounted. Inside space of the casing 121 and the inside space of the barrel 122 are communicated with a nitrogen supplying device, not shown, through tubes 126a and 126b, and also they are communicated with a gas discharging device, not shown, through tubes 127a and 127b. By continuous or interrupted nitrogen gas replacement, the oxygen density within the casing 121 and the barrel 122 can be maintained at low level. However, the spaces separated within the barrel 122 are in a closed state, and it can be considered that there is substantially no flow of gas or air between them.

In consideration of this, in the present embodiment, for circulation of nitrogen within these spaces, end portions of the lenses 123a - 123d outside the effective light flux are removed to positively provide a flow passage there. Figure 8 shows examples

wherein lens portions outside the effective light flux are removed. In Figure 8, denoted at 131 is a lens, denoted at 132 is the effective light flux range, and denoted at 133 is a notch.

5 As shown in Figure 7, the lenses 123a - 123d with notches are disposed with shift so that the flow path does not extend along a straight line. This ensures that the nitrogen gas can be supplied into the whole spaces 124a - 124e uniformly. The projection
10 lens 104 may have a similar structure, by which nitrogen circulation within the whole spaces separated by lenses can be accomplished.

 In accordance with the embodiments of the present invention as described above, a flow path for
15 circulation of inert gas such as nitrogen within the spaces separated by lenses inside a barrel can be provided with a simple design and without an increase in size of a barrel or lens.

 Next, an embodiment of device manufacturing
20 method which is based on an exposure apparatus or exposure method such as described above, will be explained.

 Figure 9 is a flow chart of procedure for manufacture of microdevices such as semiconductor
25 chips (e.g. ICs or LSIs), liquid crystal panels, CCDs, thin film magnetic heads or micro-machines, for example. Step 1 is a design process for designing a

circuit of a semiconductor device. Step 2 is a process for making a mask on the basis of the circuit pattern design. Step 3 is a process for preparing a wafer by using a material such as silicon. Step 4 is a wafer process which is called a pre-process wherein, by using the so prepared mask and wafer, circuits are practically formed on the wafer through lithography. Step 5 subsequent to this is an assembling step which is called a post-process wherein the wafer having been processed by step 4 is formed into semiconductor chips. This step includes assembling (dicing and bonding) process and packaging (chip sealing) process. Step 6 is an inspection step wherein operation check, durability check and so on for the semiconductor devices provided by step 5, are carried out. With these processes, semiconductor devices are completed and they are shipped (step 7).

Figure 10 is a flow chart showing details of the wafer process. Step 11 is an oxidation process for oxidizing the surface of a wafer. Step 12 is a CVD process for forming an insulating film on the wafer surface. Step 13 is an electrode forming process for forming electrodes upon the wafer by vapor deposition. Step 14 is an ion implanting process for implanting ions to the wafer. Step 15 is a resist process for applying a resist (photosensitive material) to the wafer. Step 16 is an exposure

process for printing, by exposure, the circuit pattern
of the mask on the wafer through the exposure
apparatus described above. Step 17 is a developing
process for developing the exposed wafer. Step 18 is
5 an etching process for removing portions other than
the developed resist image. Step 19 is a resist
separation process for separating the resist material
remaining on the wafer after being subjected to the
etching process. By repeating these processes,
10 circuit patterns are superposedly formed on the wafer.

With these processes, high density
microdevices can be manufactured.

While the invention has been described with
reference to the structures disclosed herein, it is
15 not confined to the details set forth and this
application is intended to cover such modifications or
changes as may come within the purposes of the
improvements or the scope of the following claims.

20

25

WHAT IS CLAIMED IS:

1. An exposure apparatus, comprising:
an illumination optical system for
illuminating an original with ultraviolet light;
5 a projection optical system for projecting a
pattern of the original onto a substrate to be
exposed; and
gas purging means for replacing an inside
space, where optical components of at least one of
10 said illumination optical system and said projection
optical system are placed, with a gas containing
substantially no water content.
2. An apparatus according to Claim 1, wherein
15 said gas purging means includes a sensor for detecting
the level of gas replacement and control means for
controlling gas purging on the basis of an output
signal of said sensor.
- 20 3. An apparatus according to Claim 2, wherein
said sensor comprises a hygrometer disposed in said
inside space.
4. An apparatus according to Claim 1, wherein
25 the gas containing substantially no water content
consists of one of N₂ gas, He gas and dry air.

5. An apparatus according to Claim 1, further comprising passage means for mutually communicating spaces separated by said optical components, for gas purging.

5

6. An exposure apparatus, comprising:
an illumination optical system for illuminating an original with ultraviolet light;
a projection optical system for projecting a
10 pattern of the original onto a substrate to be exposed;

gas purging means for replacing an inside space, where optical components of at least one of said illumination optical system and said projection
15 optical system are placed, with a particular gas; and

passage means for mutually communicating spaces separated by said optical components, for gas purging.

20 7. An apparatus according to Claim 6, wherein said particular gas consists of an inert gas.

8. An apparatus according to Claim 6, wherein said optical components include a lens, wherein said
25 apparatus further comprises a support for supporting said lens, and wherein said passage means for gas purging comprises an aperture formed in said support.

9. An apparatus according to Claim 6, wherein
said optical components include a lens, and wherein
said passage means for gas purging comprises a notch
5 provided on said lens.

10. An apparatus according to Claim 6, wherein a
straight line connecting adjacent passage means
provided in one and the same casing for gas purging,
10 extends out of parallel to an optical axis of a lens
which is one of the optical components.

11. An apparatus according to Claim 1 or 6,
wherein a path is defined within the space for gas
15 flowing from a gas inlet to a gas outlet, for gas
purging.

12. An apparatus according to Claim 1 or 6,
further comprising a light source having one of a KrF
20 excimer laser, a ArF excimer laser and F₂ excimer
laser.

13. A device manufacturing method for
manufacturing a device by use of an exposure apparatus
25 as recited in any one of Claims 1 - 12.

An exposure apparatus includes an illumination optical system for illuminating an original with ultraviolet light, a projection optical system for projecting a pattern of the original onto a substrate to be exposed, and a gas purging device for replacing an inside space, where optical components of at least one of the illumination optical system and the projection optical system are placed, with a gas containing substantially no water content or an inert gas.

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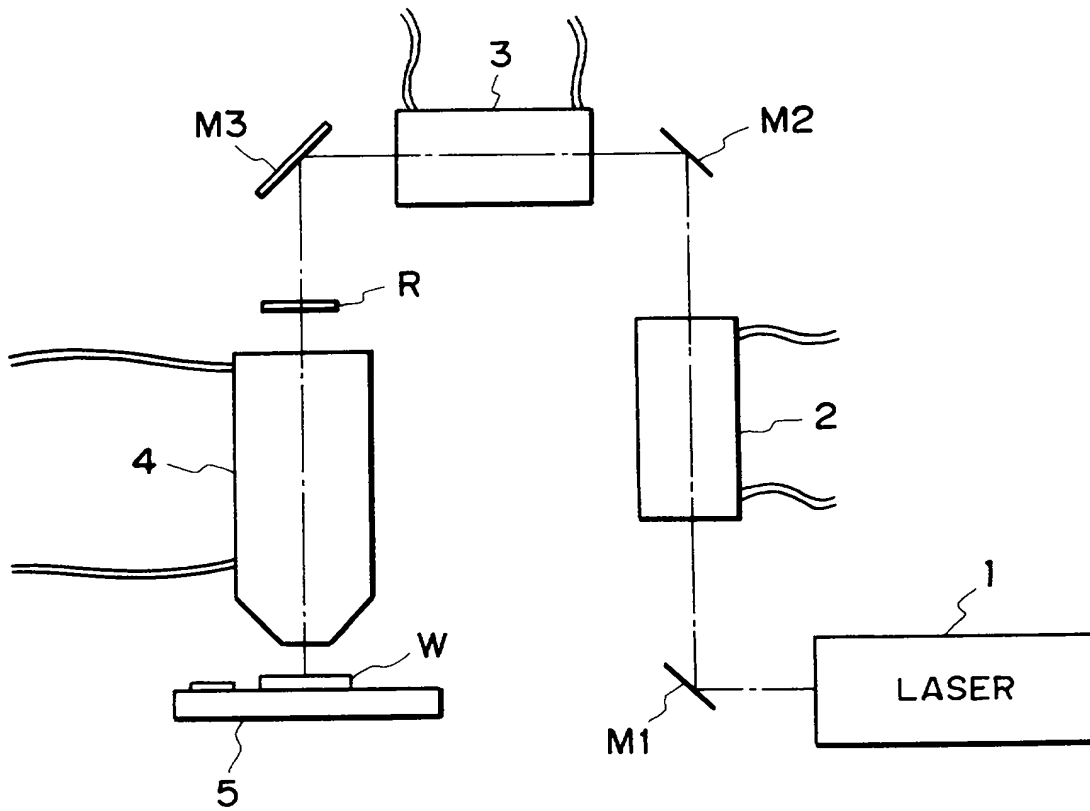


FIG. 1

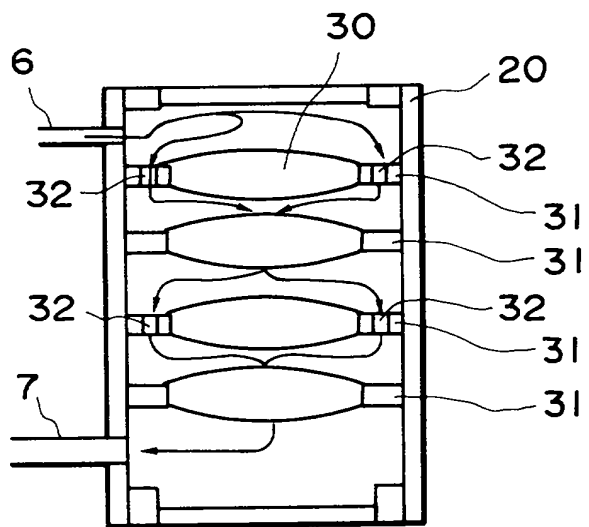


FIG. 2

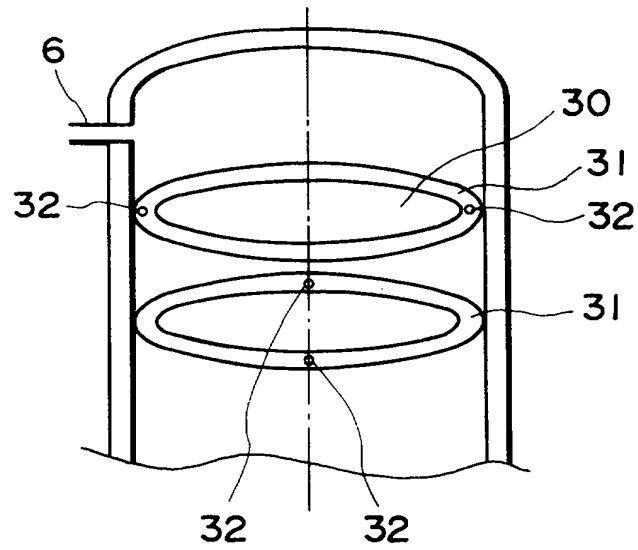


FIG. 3

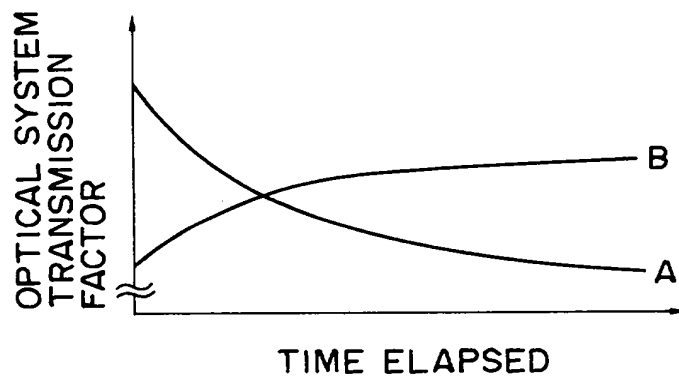
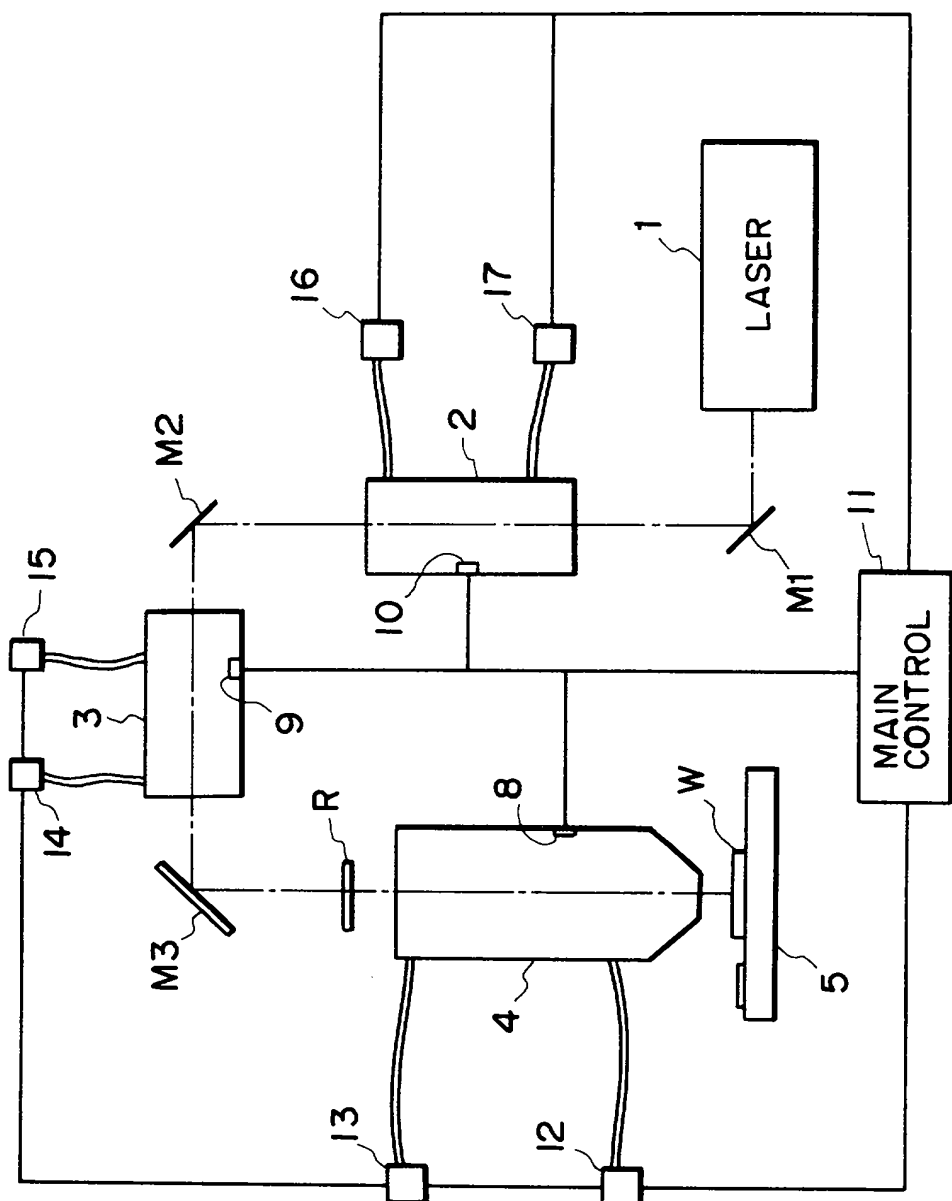


FIG. 4



56F

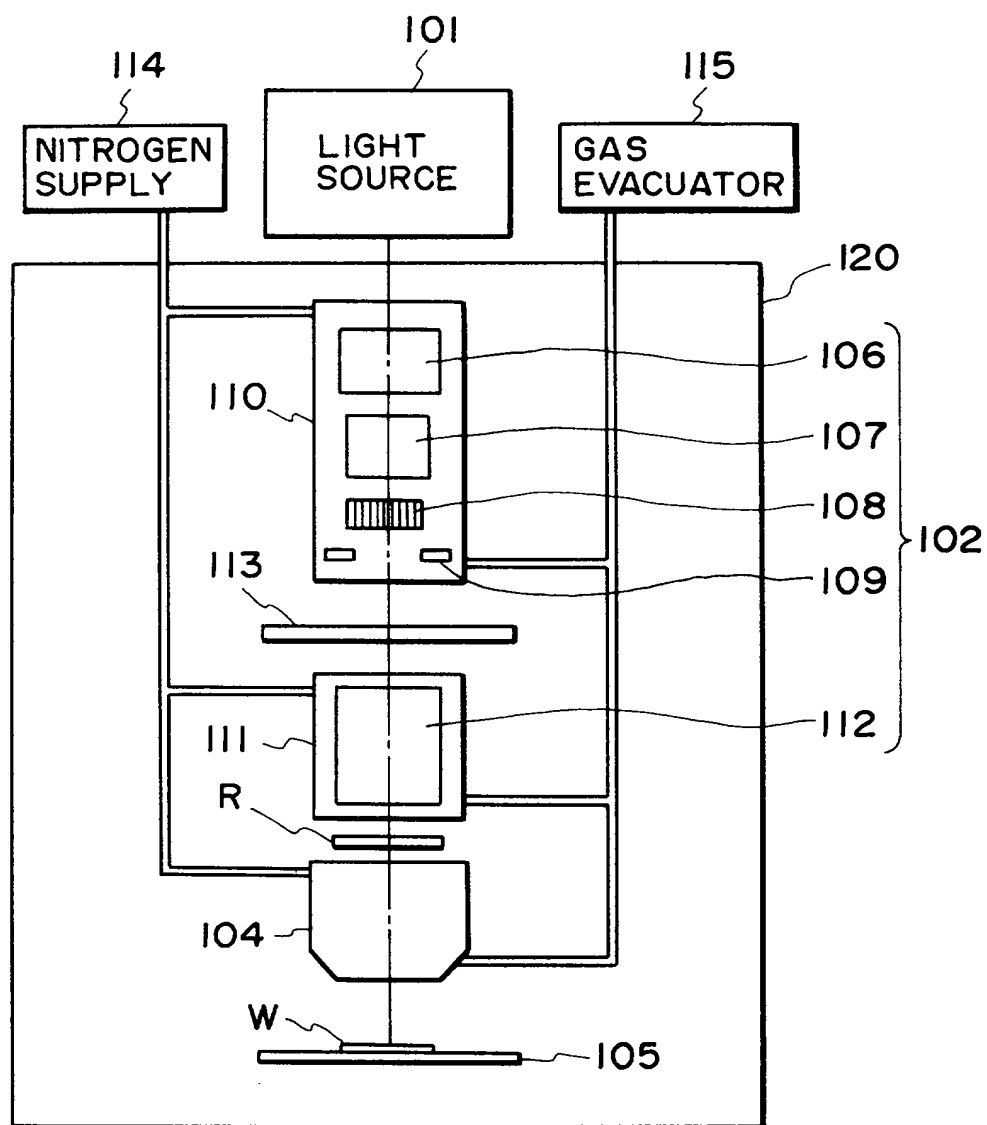


FIG. 6

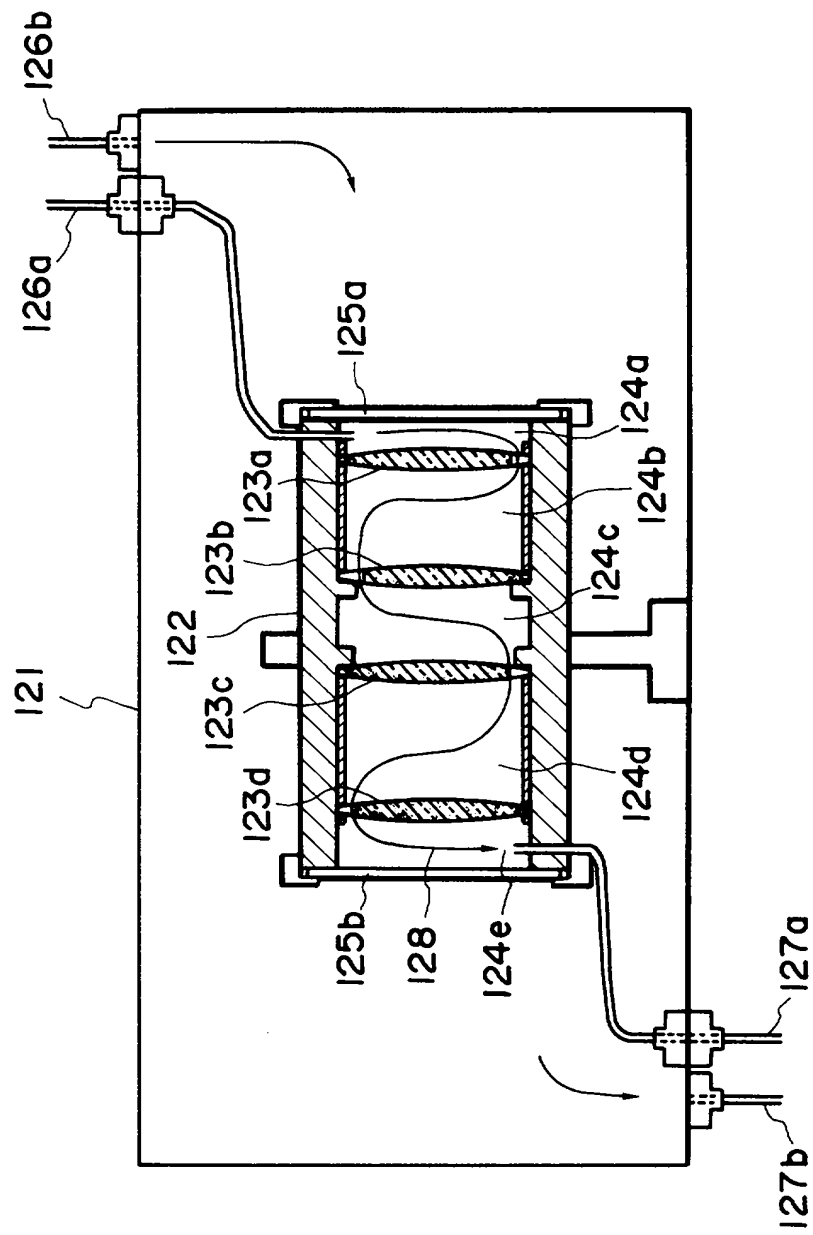


FIG. 7

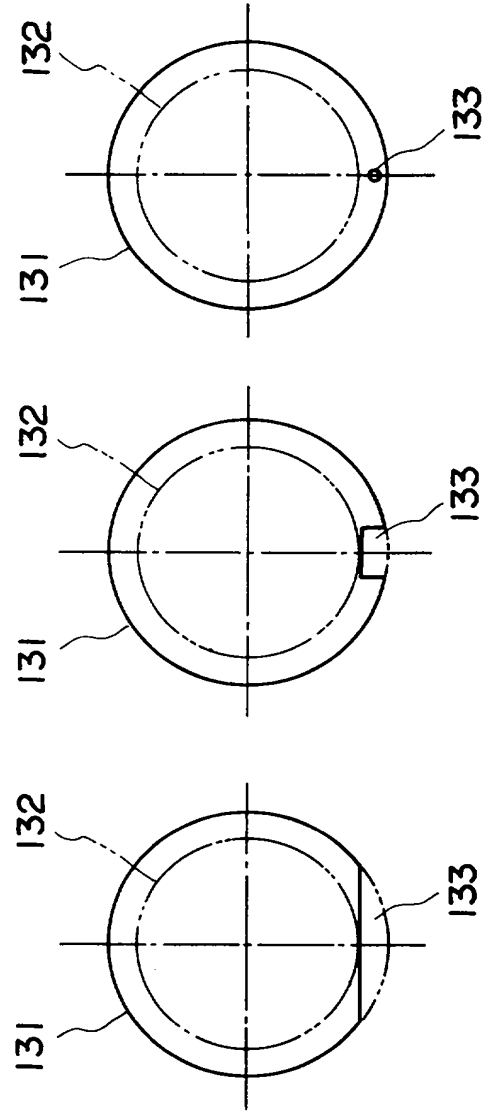


FIG. 8

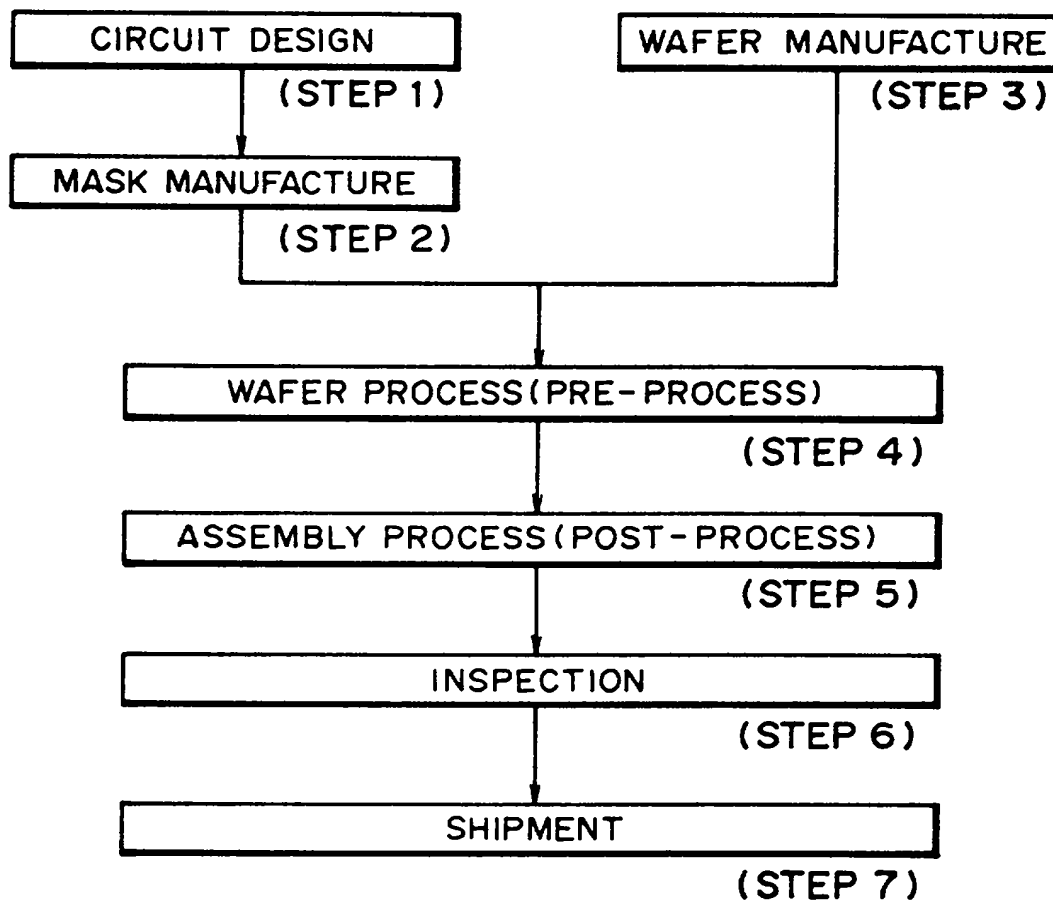


FIG. 9

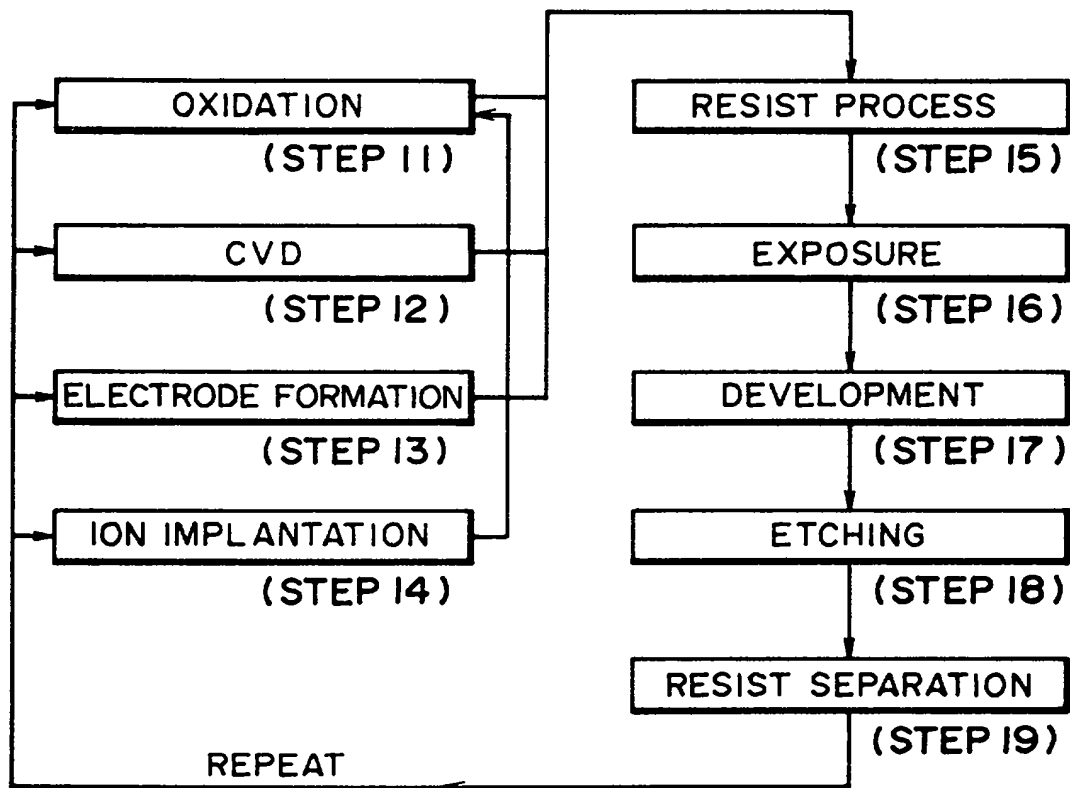


FIG. 10

**COMBINED DECLARATION AND POWER OF ATTORNEY
FOR PATENT APPLICATION**

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name;

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled _____

EXPOSURE APPARATUS AND DEVICE MANUFACTURING METHOD

the specification of which ☒ is attached hereto ☐ was filed on _____ as United States Application No. or PCT International Application No. _____ and was amended on _____ (if applicable).

I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims, as amended by any amendment referred to above.

I acknowledge the duty to disclose information which is material to patentability as defined in 37 CFR §1.56.

I hereby claim foreign priority benefits under 35 U.S.C. §119(a)-(d) or §365(b), of any foreign application(s) for patent or inventor's certificate, or § 365(a) of any PCT international application which designates at least one country other than the United States, listed below and have also identified below any foreign application for patent or inventor's certificate, or PCT international application having a filing date before that of the application on which priority is claimed:

Country	Application No.	Filed (Day/Mo./Yr.)	(Yes/No) Priority Claimed
JAPAN	09-254130	September 4, 1997	Yes
JAPAN	10-219906	July 21, 1998	Yes

I hereby claim the benefit under 35 U.S.C. § 120 of any United States application(s), or § 365(c) of any PCT international application designating the United States, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States or PCT international application in the manner provided by the first paragraph of 35 U.S.C. § 112, I acknowledge the duty to disclose information which is material to patentability as defined in 37 C.F.R. § 1.56 which became available between the filing date of the prior application and the national or PCT international filing date of this application.

Application No.	Filed (Day/Mo./Yr.)	Status (Patented, Pending, Abandoned)
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I hereby appoint the practitioners associated with the firm and Customer Number provided below to prosecute this application and to transact all business in the Patent and Trademark Office connected therewith, and direct that all correspondence be addressed to the address associated with that Customer Number:

FITZPATRICK, CELLA, HARPER & SCINTO
Customer Number: 05514

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Full Name of Sole or First Inventor TOMOHARU HASE

Inventor's signature _____

Date _____ Citizen/Subject of JAPAN

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